N-Channel 20 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)[a]
20	0.0060 at V_{GS} = 10 V	26
	0.0095 at V_{GS} = 4.5 V	21

FEATURES

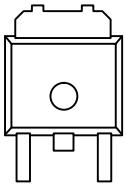
- TrenchFET® Power MOSFET
- 175 °C Junction Temperature
- PWM Optimized for High Efficiency
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC

RoHS COMPLIANT

APPLICATIONS

- Synchronous Buck DC/DC Conversion
  - Desktop
  - Server

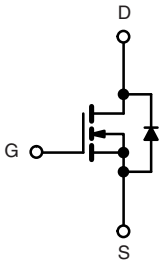
TO-252



Top View

Drain Connected to Tab

Ordering Information: SUD50N02-06P-E3 (Lead (Pb) free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	20	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current[a]	T_A = 25 °C	I_D	26[a]	A
	T_C = 25 °C		50[b]	
Pulsed Drain Current		I_{DM}	100	
Continuous Source Current (Diode Conduction)[a]		I_S	26	
Avalanche Current	L = 0.1 mH	I_{AS}	45	
Single Pulse Avalanche Energy		E_{AS}	101	mJ
Maximum Power Dissipation	T_A = 25 °C	P_D	6.8[a]	W
	T_C = 25 °C		65	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient[a]	t ≤ 10 s	R_{thJA}	18	22	°C/W
	Steady State		40	50	
Maximum Junction-to-Case		R_{thJC}	1.9	2.3	

Notes:
a. Surface mounted on FR4 board, t ≤ 10 s.
b. Limited by package.

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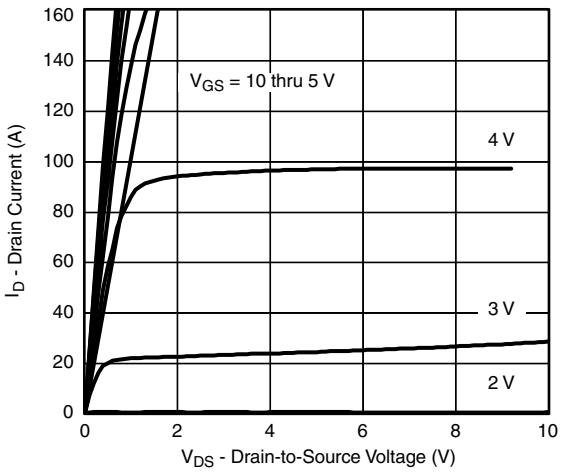
SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.[a]**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	20			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	0.8		3	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 20 V, V_{GS} = 0 V			1	µA
		V_{DS} = 20 V, V_{GS} = 0 V, T_J = 125 °C			50	
On-State Drain Current[b]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 10 V	50			A
Drain-Source On-State Resistance[b]	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 20 A		0.0046	0.006	Ω
		V_{GS} = 10 V, I_D = 20 A, T_J = 125 °C			0.0084	
		V_{GS} = 4.5 V, I_D = 20 A		0.0073	0.0095	
Forward Transconductance[b]	g_{fs}	V_{DS} = 15 V, I_D = 20 A	15			S
Dynamic[a]						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 10 V, f = 1 MHz		2550		pF
Output Capacitance	C_{oss}			900		
Reverse Transfer Capacitance	C_{rss}			415		
Total Gate Charge[c]	Q_g	V_{DS} = 10 V, V_{GS} = 4.5 V, I_D = 50 A		19	30	nC
Gate-Source Charge[c]	Q_{gs}			7.5		
Gate-Drain Charge[c]	Q_{gd}			6		
Gate Resistance	R_g		0.5	1.5	2.4	Ω
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = 10 V, R_L = 0.2 Ω I_D ≅ 50 A, V_{GEN} = 10 V, R_G = 2.5 Ω		11	20	ns
Rise Time[c]	t_r			10	15	
Turn-Off Delay Time[c]	$t_{d(off)}$			24	35	
Fall Time[c]	t_f			9	15	
Source-Drain Diode Ratings and Characteristic (T_C = 25 °C)						
Pulsed Current	I_{SM}				100	A
Diode Forward Voltage[b]	V_{SD}	I_F = 50 A, V_{GS} = 0 V		1.2	1.5	V
Source-Drain Reverse Recovery Time	t_{rr}	I_F = 50 A, dI/dt = 100 A/µs		35	70	ns

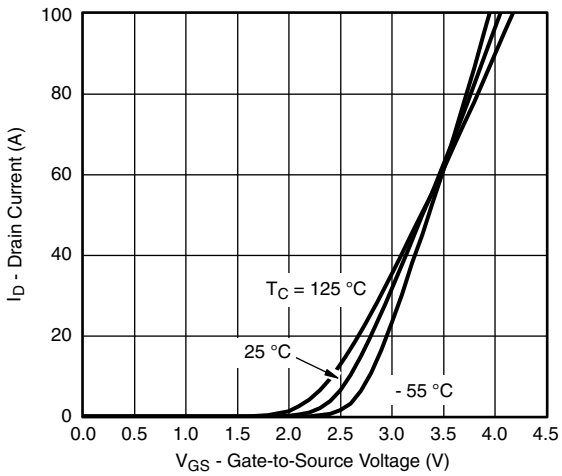
Notes:
a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C unless noted)



Output Characteristics



Transfer Characteristics

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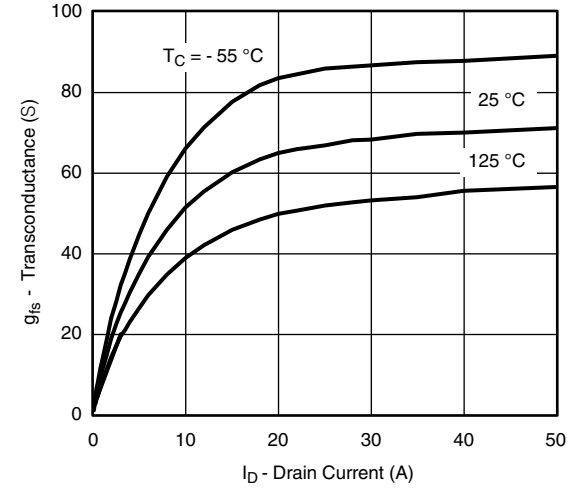
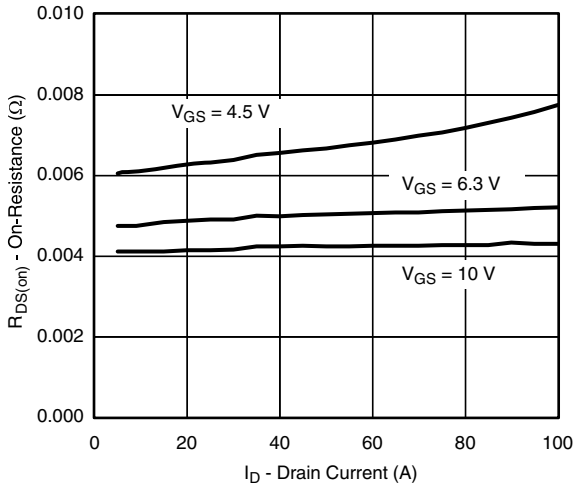
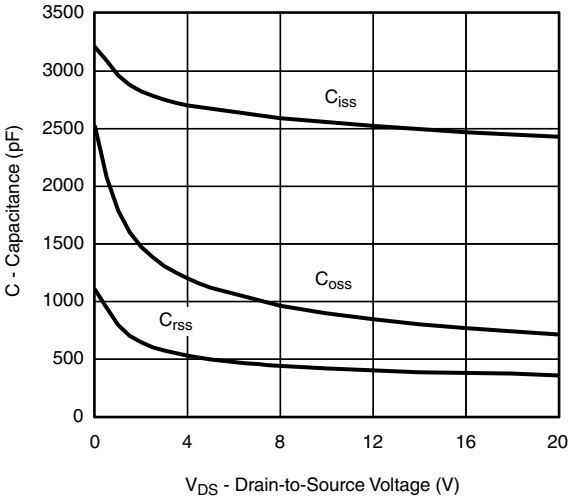
TYPICAL CHARACTERISTICS (25 °C unless noted)



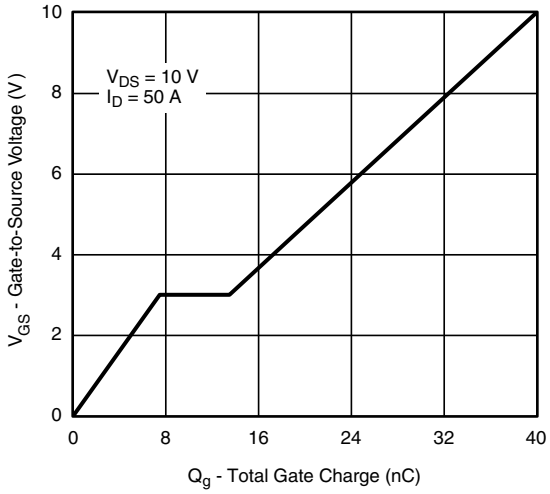
Transconductance



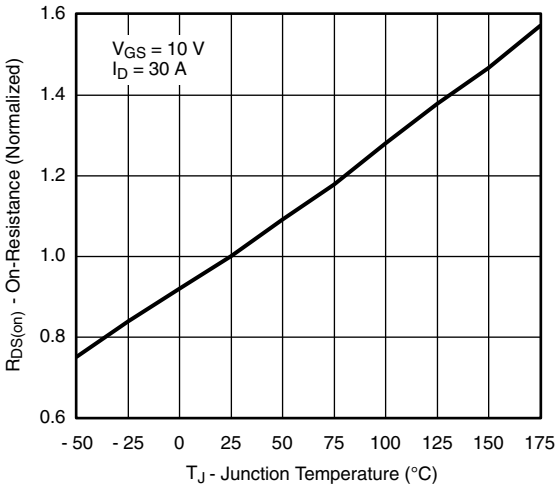
On-Resistance vs. Drain Current



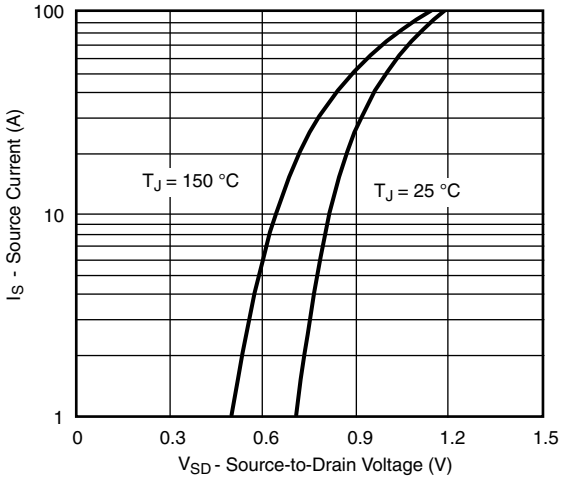
Capacitance



Gate Charge



On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

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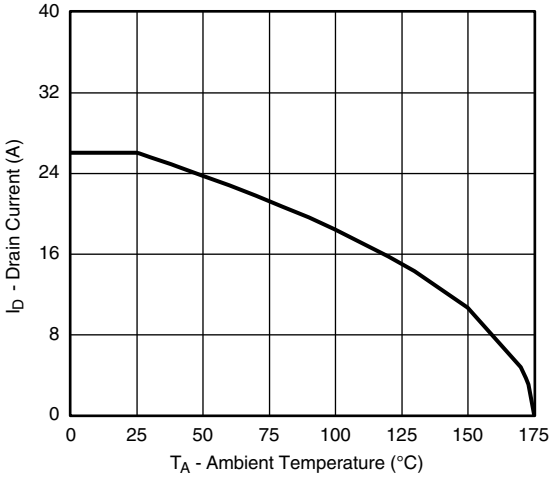
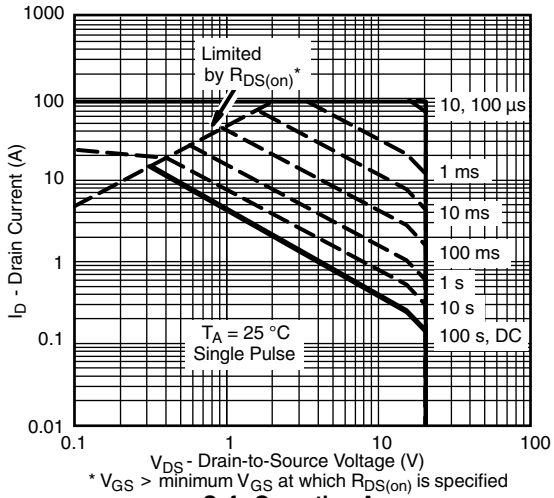
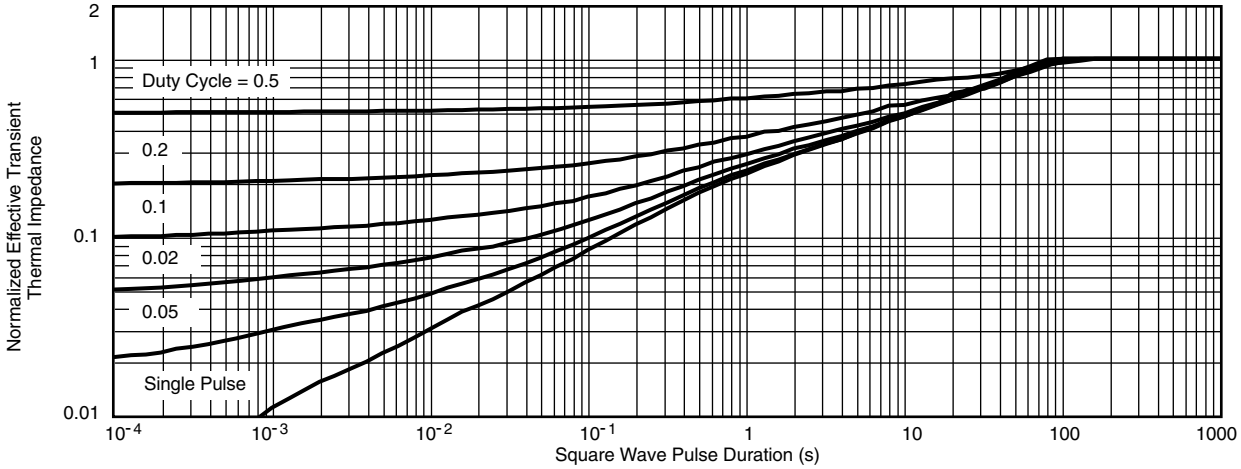
THERMAL RATINGS



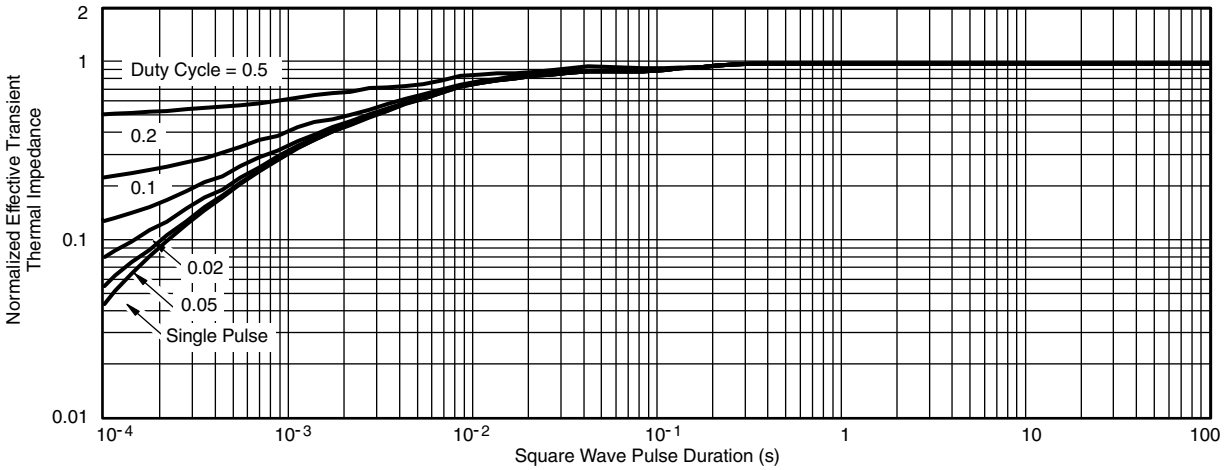
Maximum Drain Current vs. Ambient Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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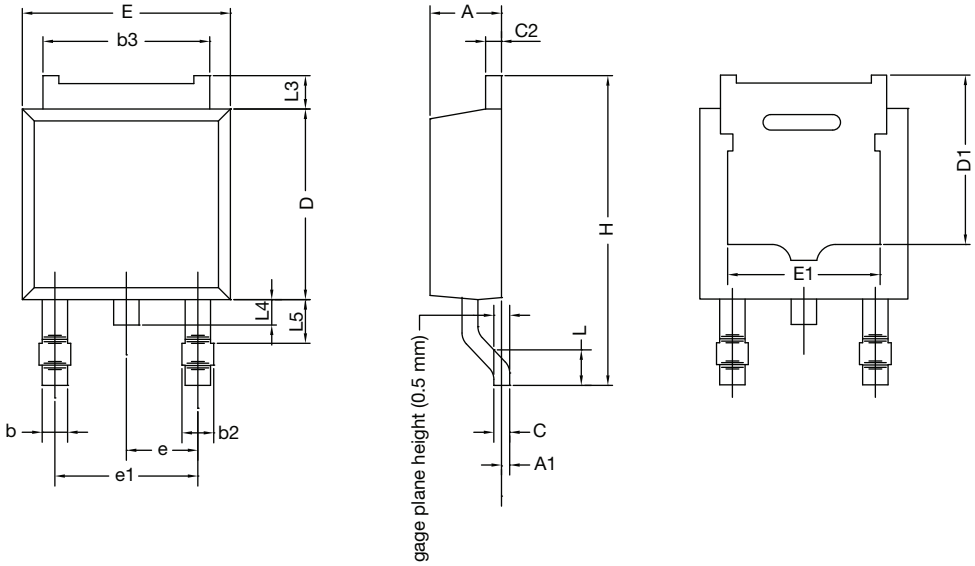
TO-252AA Case Outline

VERSION 1: FACILITY CODE = Y



	MILLIMETERS	
DIM.	MIN.	MAX.
A	2.18	2.38
A1	-	0.127
b	0.64	0.88
b2	0.76	1.14
b3	4.95	5.46
C	0.46	0.61
C2	0.46	0.89
D	5.97	6.22
D1	4.10	-
E	6.35	6.73
E1	4.32	-
H	9.40	10.41
e	2.28 BSC	
e1	4.56 BSC	
L	1.40	1.78
L3	0.89	1.27
L4	-	1.02
L5	1.01	1.52

Note

- Dimension L3 is for reference only

For technical questions, contact: pmostechsupport@vishay.com

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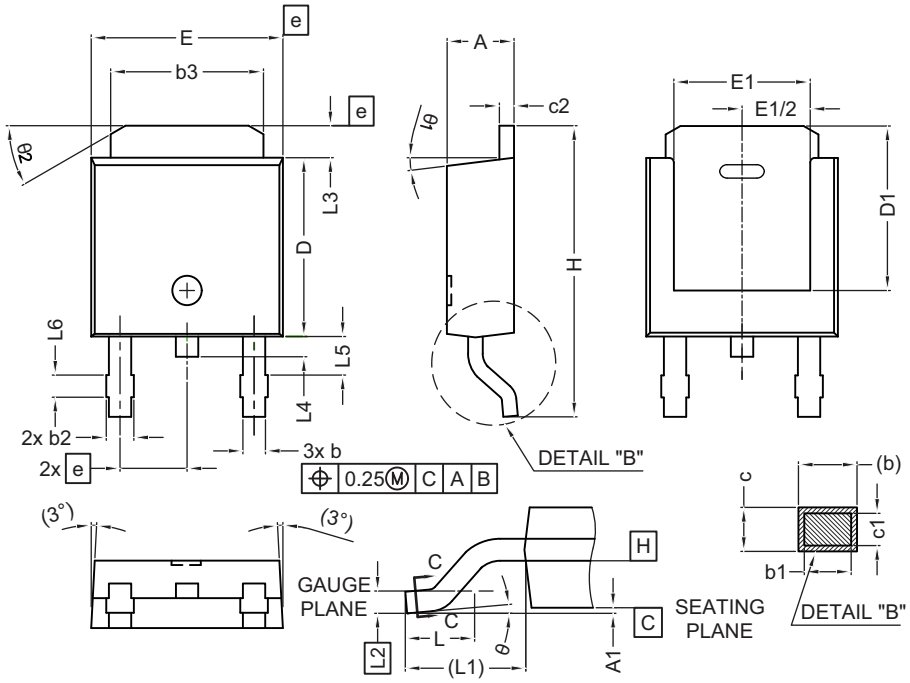

	MILLIMETERS	
DIM.	MIN.	MAX.
A	2.18	2.39
A1	-	0.13
b	0.65	0.89
b1	0.64	0.79
b2	0.76	1.13
b3	4.95	5.46
c	0.46	0.61
c1	0.41	0.56
c2	0.46	0.60
D	5.97	6.22
D1	5.21	-
E	6.35	6.73
E1	4.32	-
e	2.29 BSC	
H	9.94	10.34

	MILLIMETERS	
DIM.	MIN.	MAX.
L	1.50	1.78
L1	2.74 ref.	
L2	0.51 BSC	
L3	0.89	1.27
L4	-	1.02
L5	1.14	1.49
L6	0.65	0.85
θ	0°	10°
θ1	0°	15°
θ2	25°	35°

Notes

- Dimensioning and tolerance confirm to ASME Y14.5M-1994
- All dimensions are in millimeters. Angles are in degrees
- Heat sink side flash is max. 0.8 mm
- Radius on terminal is optional

ECN: E22-0399-Rev. R, 03-Oct-2022
DWG: 5347

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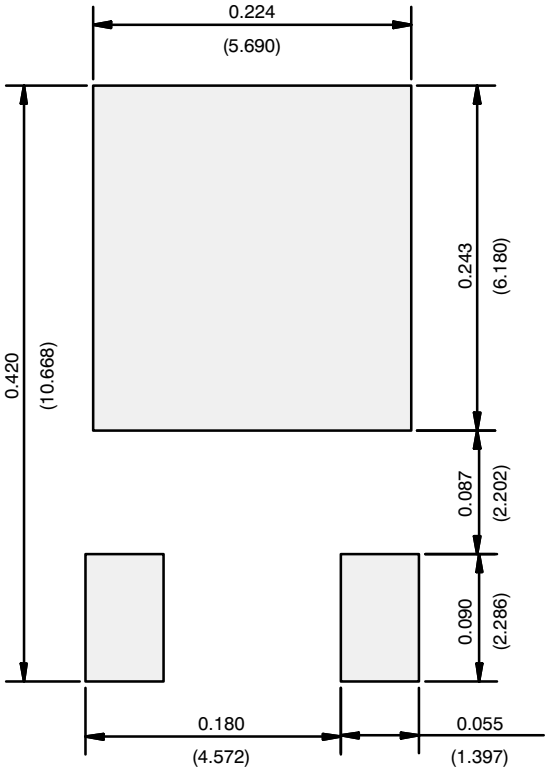
RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads
Dimensions in Inches/(mm)

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